

CSD19506KCS 80 V N-Channel NexFET™ Power MOSFET

1 Features

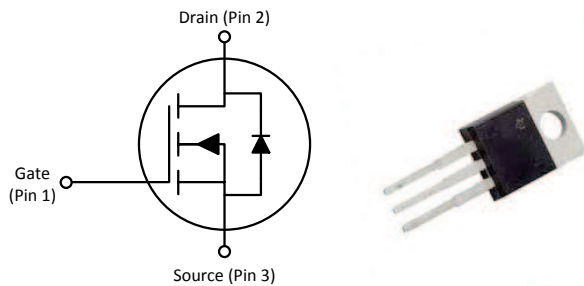
- Ultra-Low Q_g and Q_{gd}
- Low Thermal Resistance
- Avalanche Rated
- Pb-Free Terminal Plating
- RoHS Compliant
- Halogen Free
- TO-220 Plastic Package

2 Applications

- Secondary Side Synchronous Rectifier
- Motor Control

3 Description

This 80 V, 2.0 mΩ, TO-220 NexFET™ power MOSFET is designed to minimize losses in power conversion applications.



Product Summary

$T_A = 25^\circ\text{C}$		TYPICAL VALUE		UNIT
V_{DS}	Drain-to-Source Voltage	80		V
Q_g	Gate Charge Total (10 V)	120		nC
Q_{gd}	Gate Charge Gate to Drain	20		nC
$R_{DS(on)}$	Drain-to-Source On Resistance	$V_{GS} = 6\text{ V}$	2.2	mΩ
		$V_{GS} = 10\text{ V}$	2.0	mΩ
$V_{GS(th)}$	Threshold Voltage	2.5		V

Ordering Information⁽¹⁾

Device	Package	Media	Qty	Ship
CSD19506KCS	TO-220 Plastic Package	Tube	50	Tube

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Absolute Maximum Ratings

$T_A = 25^\circ\text{C}$		VALUE	UNIT
V_{DS}	Drain-to-Source Voltage	80	V
V_{GS}	Gate-to-Source Voltage	± 20	V
I_D	Continuous Drain Current (Package limited)	150	A
	Continuous Drain Current (Silicon limited), $T_C = 25^\circ\text{C}$	273	
	Continuous Drain Current (Silicon limited), $T_C = 100^\circ\text{C}$	193	
I_{DM}	Pulsed Drain Current ⁽¹⁾	400	A
P_D	Power Dissipation	375	W
T_J, T_{stg}	Operating Junction and Storage Temperature Range	-55 to 175	$^\circ\text{C}$
E_{AS}	Avalanche Energy, single pulse $I_D = 129\text{ A}, L = 0.1\text{ mH}, R_G = 25\ \Omega$	832	mJ

(1) Max $R_{\theta JC} = 0.4^\circ\text{C/W}$, pulse duration $\leq 100\ \mu\text{s}$, duty cycle $\leq 1\%$

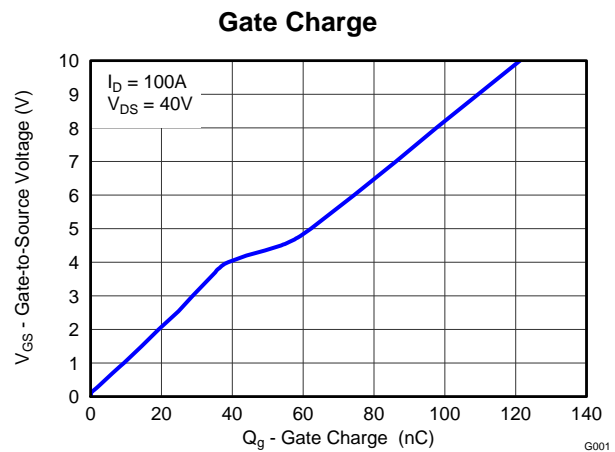
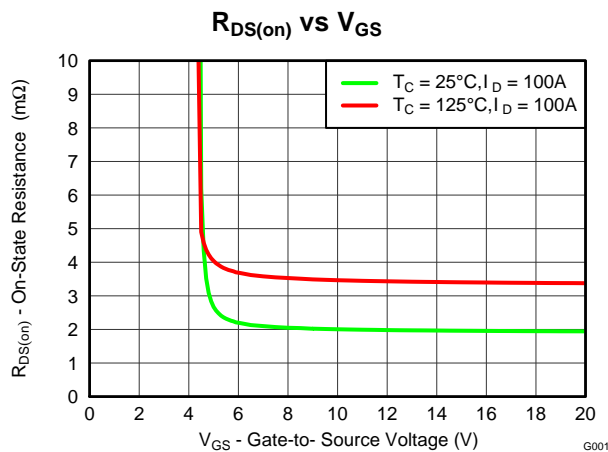


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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision A (February 2014) to Revision B	Page
• Changed Pulsed Drain Current Conditions	1
• Updated the SOA in Figure 10	6

Changes from Original (December 2013) to Revision A	Page
• Increased Package Current Limit to 150 A	1
• Increased Pulsed Drain Current to 400 A	1
• Updated SOA Curve	5

5 Specifications

5.1 Electrical Characteristics

($T_A = 25^\circ\text{C}$ unless otherwise stated)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
STATIC CHARACTERISTICS						
V_{DSS}	Drain-to-Source Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	80			V
I_{DSS}	Drain-to-Source Leakage Current	$V_{GS} = 0\text{ V}, V_{DS} = 64\text{ V}$			1	μA
I_{GSS}	Gate-to-Source Leakage Current	$V_{DS} = 0\text{ V}, V_{GS} = 20\text{ V}$			100	nA
$V_{GS(th)}$	Gate-to-Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2.1	2.5	3.2	V
$R_{DS(on)}$	Drain-to-Source On-Resistance	$V_{GS} = 6\text{ V}, I_D = 100\text{ A}$		2.2	2.8	$\text{m}\Omega$
		$V_{GS} = 10\text{ V}, I_D = 100\text{ A}$		2.0	2.3	$\text{m}\Omega$
g_{fs}	Transconductance	$V_{DS} = 8\text{ V}, I_D = 100\text{ A}$		297		S
DYNAMIC CHARACTERISTICS						
C_{iss}	Input Capacitance	$V_{GS} = 0\text{ V}, V_{DS} = 40\text{ V}, f = 1\text{ MHz}$		9380	12200	pF
C_{oss}	Output Capacitance			2260	2940	pF
C_{rss}	Reverse Transfer Capacitance			42	55	pF
R_G	Series Gate Resistance			1.3	2.6	Ω
Q_g	Gate Charge Total (10 V)	$V_{DS} = 40\text{ V}, I_D = 100\text{ A}$		120	156	nC
Q_{gd}	Gate Charge Gate to Drain			20		nC
Q_{gs}	Gate Charge Gate to Source			37		nC
$Q_{g(th)}$	Gate Charge at V_{th}			25		nC
Q_{oss}	Output Charge	$V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}$		345		nC
$t_{d(on)}$	Turn On Delay Time	$V_{DS} = 40\text{ V}, V_{GS} = 10\text{ V}, I_{DS} = 100\text{ A}, R_G = 0\ \Omega$		19		ns
t_r	Rise Time			11		ns
$t_{d(off)}$	Turn Off Delay Time			30		ns
t_f	Fall Time			10		ns
DIODE CHARACTERISTICS						
V_{SD}	Diode Forward Voltage	$I_{SD} = 100\text{ A}, V_{GS} = 0\text{ V}$		0.9	1.1	V
Q_{rr}	Reverse Recovery Charge	$V_{DS} = 40\text{ V}, I_F = 100\text{ A}, di/dt = 300\text{ A}/\mu\text{s}$		525		nC
t_{rr}	Reverse Recovery Time			107		ns

5.2 Thermal Information⁽¹⁾

($T_A = 25^\circ\text{C}$ unless otherwise stated)

THERMAL METRIC		MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction-to-Case Thermal Resistance			0.4	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance			62	

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, [SPRA953](#).

5.3 Typical MOSFET Characteristics

($T_A = 25^\circ\text{C}$ unless otherwise stated)

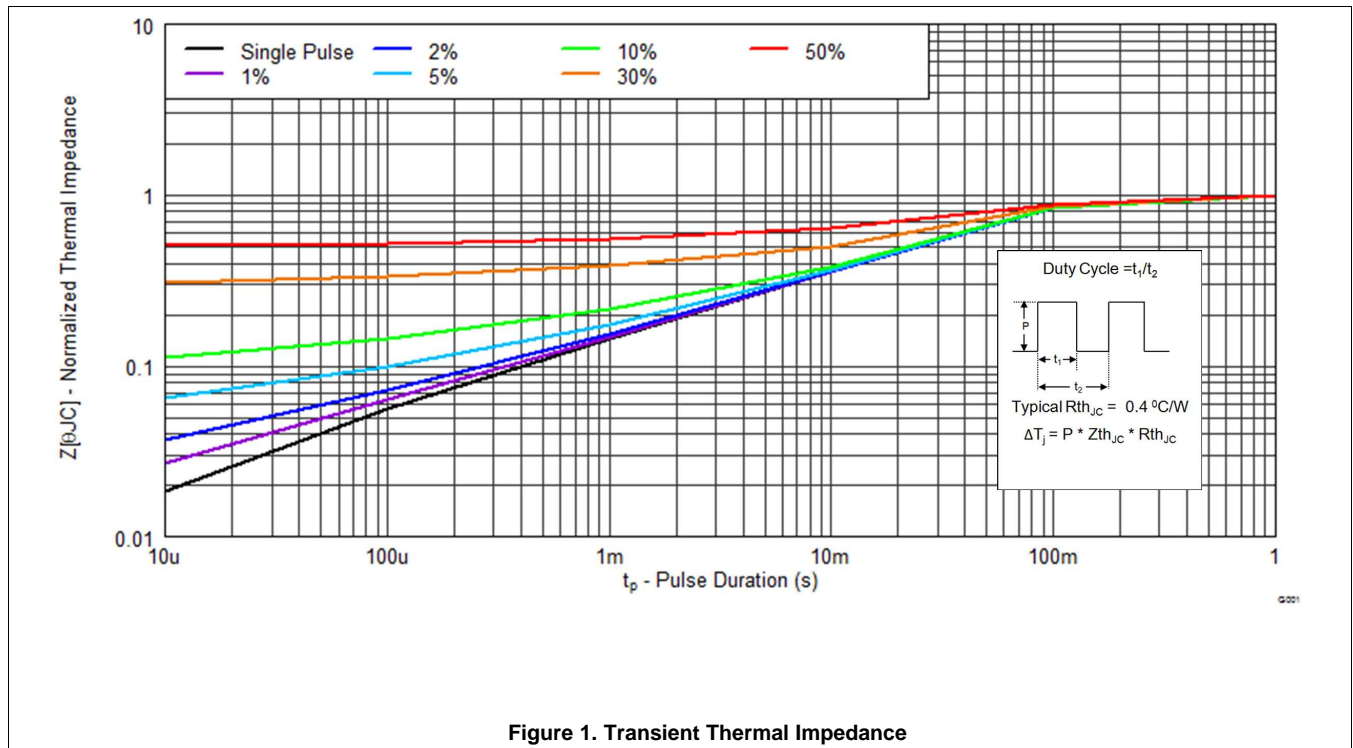


Figure 1. Transient Thermal Impedance

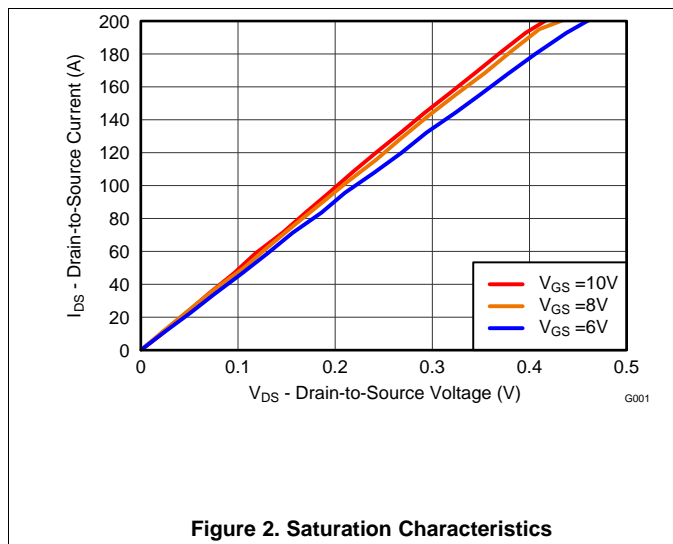


Figure 2. Saturation Characteristics

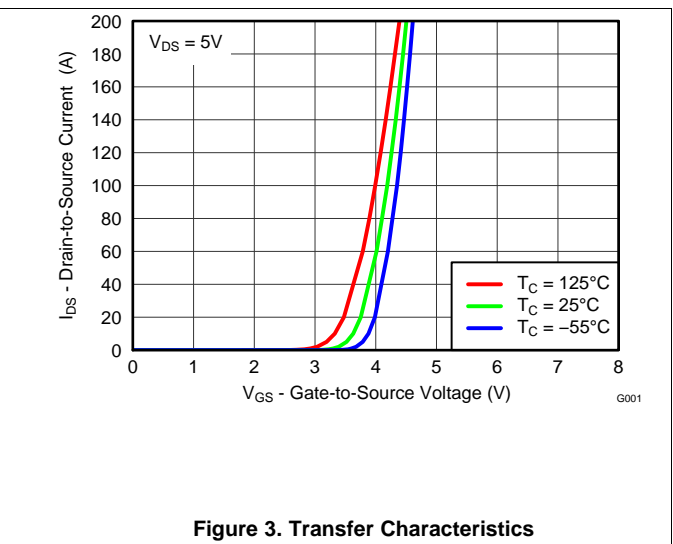
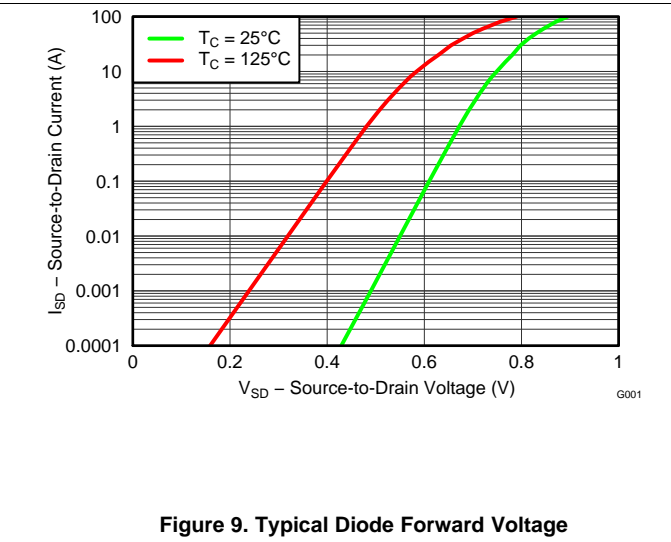
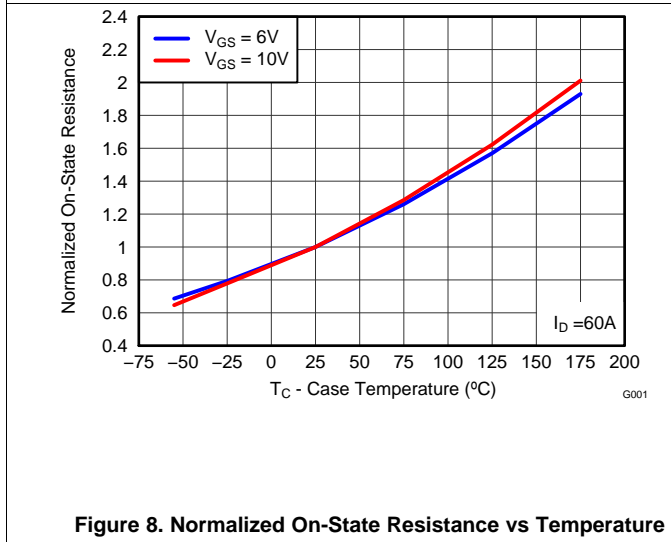
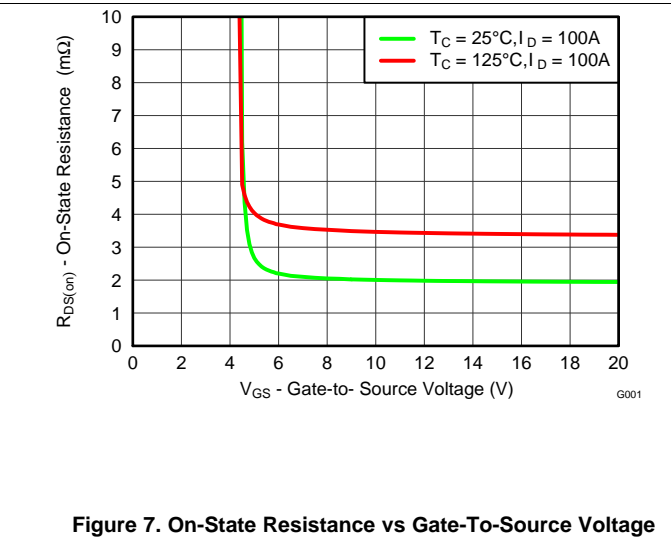
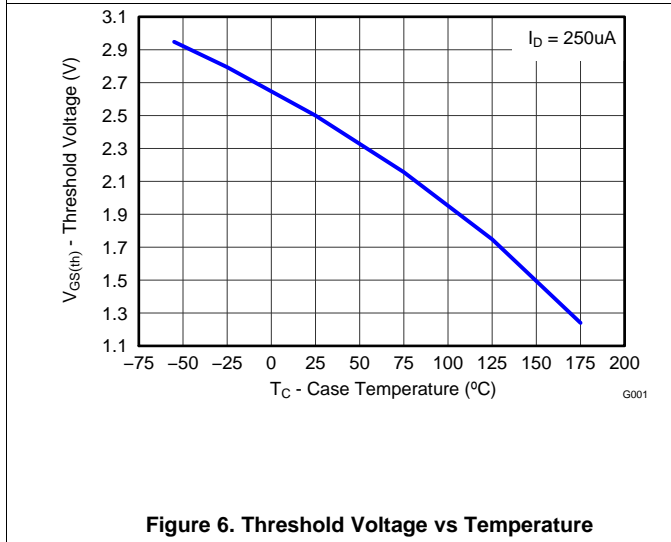
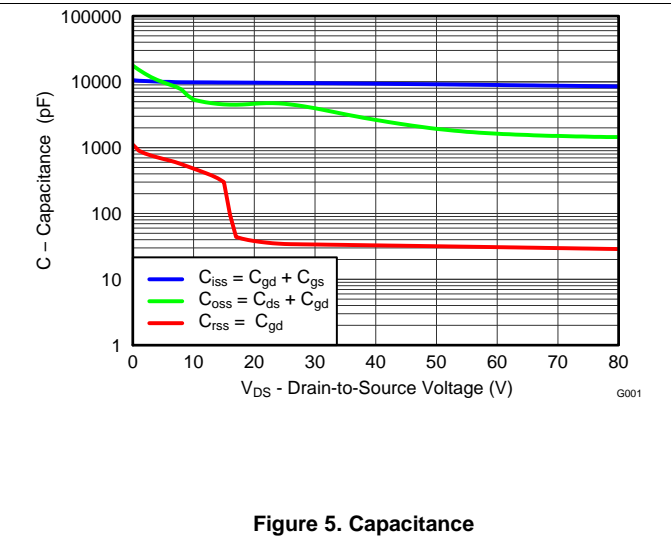
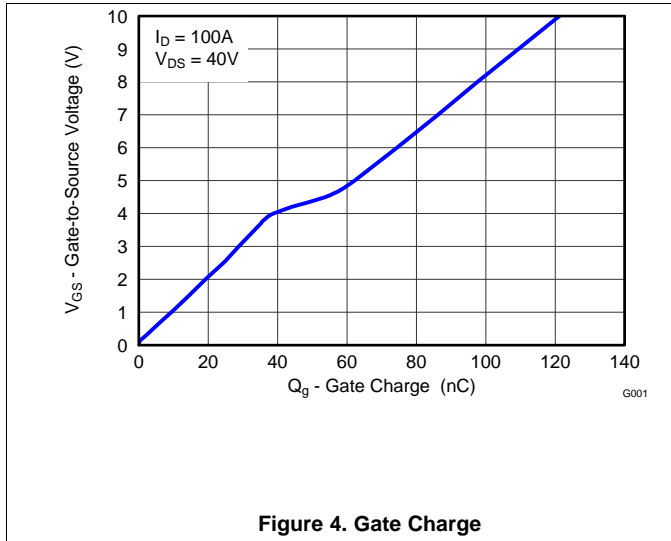


Figure 3. Transfer Characteristics

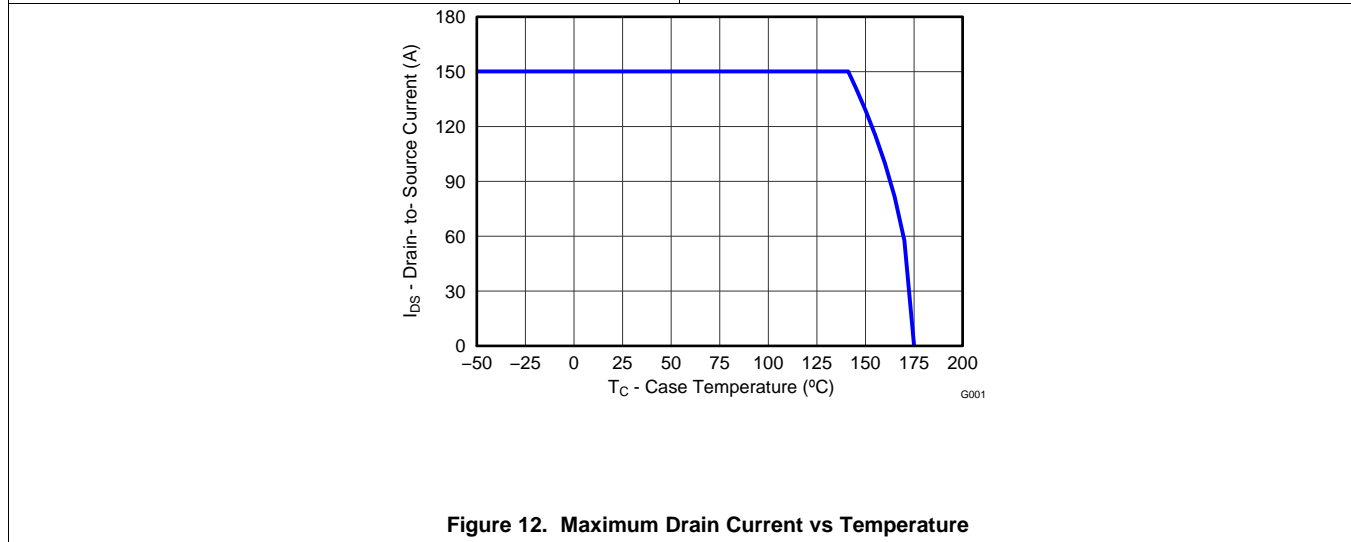
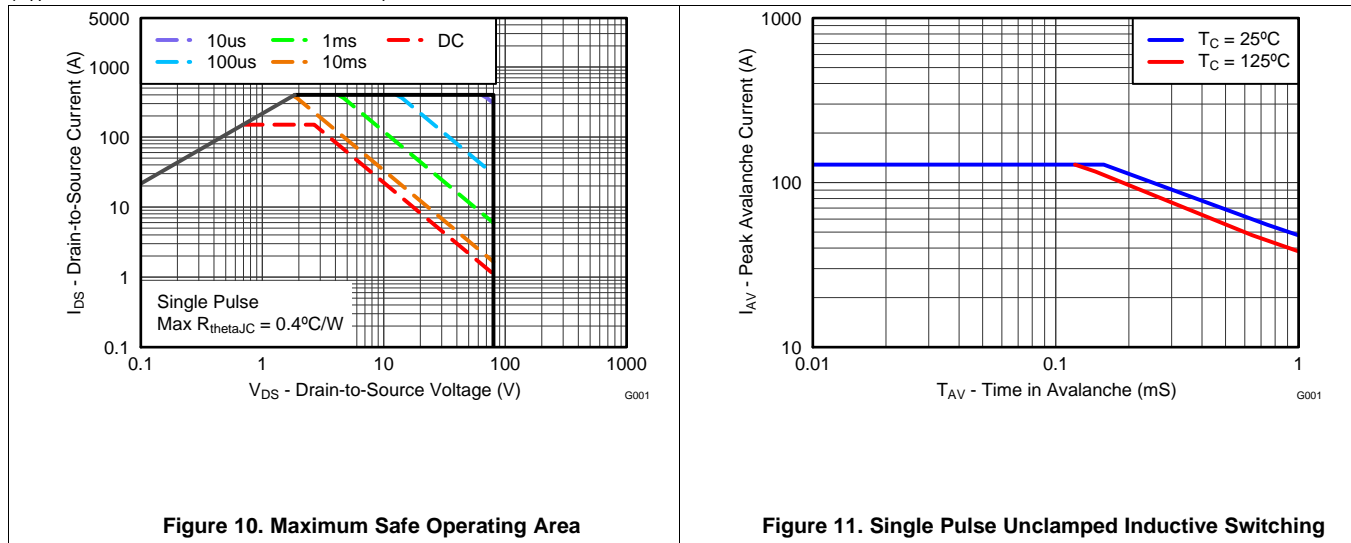
Typical MOSFET Characteristics (continued)

($T_A = 25^\circ\text{C}$ unless otherwise stated)



Typical MOSFET Characteristics (continued)

($T_A = 25^\circ\text{C}$ unless otherwise stated)



6 Device and Documentation Support

6.1 Trademarks

NexFET is a trademark of Texas Instruments.

6.2 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

6.3 Glossary

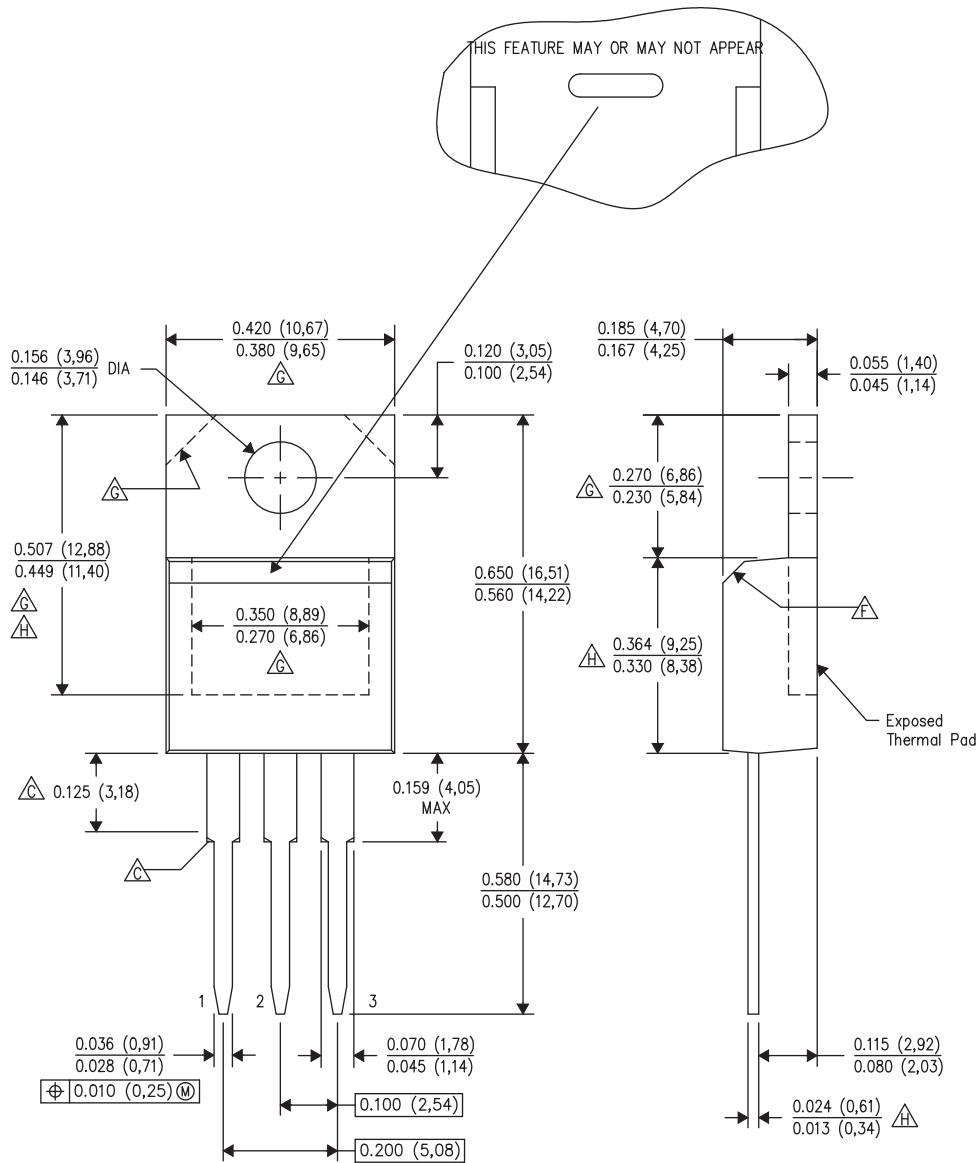
[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

7 Mechanical, Packaging, and Orderable Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

7.1 KCS Package Dimensions



- NOTES:
- A. All linear dimensions are in inches (millimeters).
 - B. This drawing is subject to change without notice.
 - C Lead dimensions are not controlled within this area. Chamfer may or may not appear
 - D. All lead dimensions apply before solder dip.
 - E. The center lead is in electrical contact with the mounting tab.
 - F. The chamfer is optional.
 - G. Thermal pad contour optional within these dimensions.
 - H. Falls within JEDEC TO-220 variation AB, except minimum lead thickness, minimum exposed pad length, and maximum body length.

Pin Configuration

Position	Designation
Pin 1	Gate
Pin 2 / Tab	Drain
Pin 3	Source

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
CSD19506KCS	ACTIVE	TO-220	KCS	3	50	Pb-Free (RoHS)	SN	N / A for Pkg Type	-55 to 175	CSD19506KCS	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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